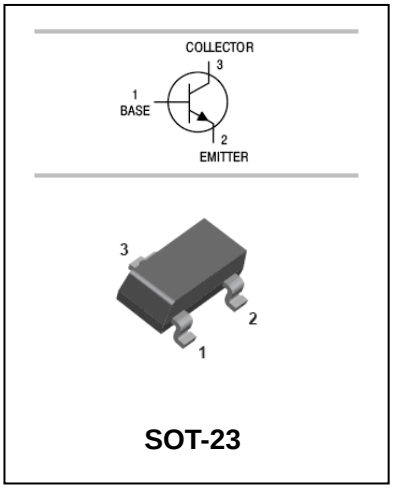
Silicon Epitaxial Planar Transistor **2SC3125**

FEATURES

- Good Linearity of f_T.

Lead-free



SOT-23

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC3125	HH	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

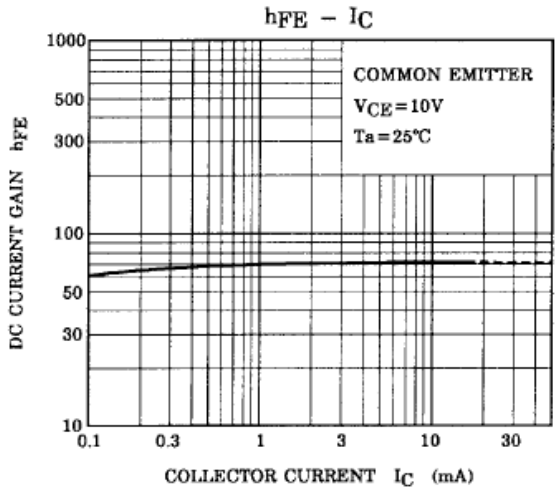
Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
I_B	Base Current	25	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +125	℃

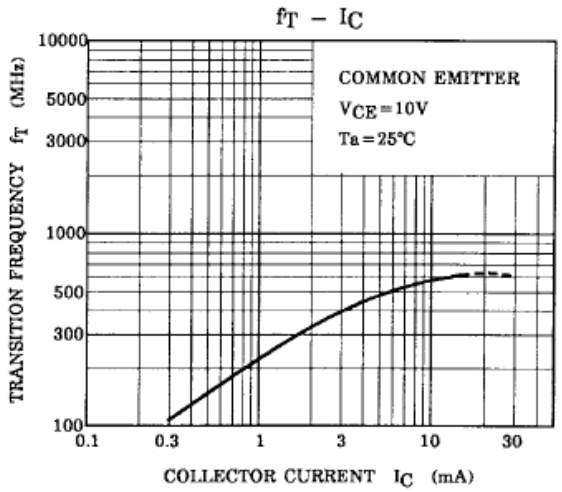
Silicon Epitaxial Planar Transistor **2SC3125**

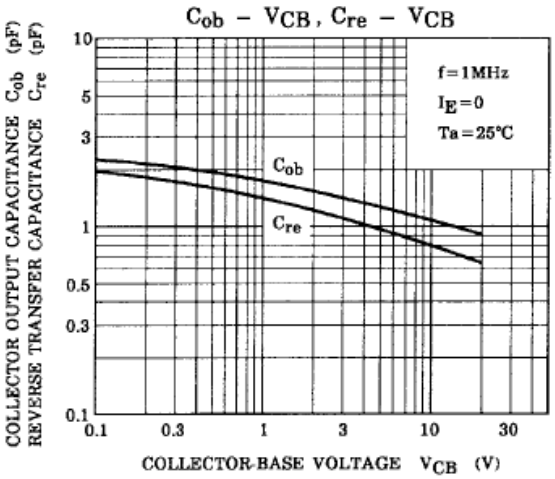
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

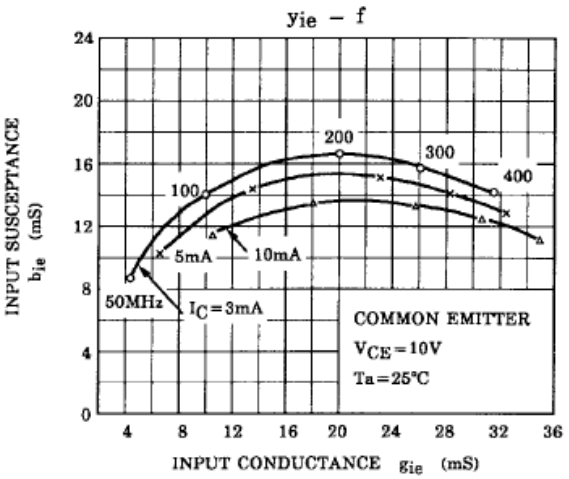
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	25			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=10V,I_C=10mA	20	70	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=15mA, I_B=1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=15mA, I_B=1.5mA			1.5	V
Transition frequency	f_T	V_{CE}=10V, I_C= 10mA	250	600		MHz
Collector-base output capacitance	C_{ob}	V_{CB}=10V, I_E=0,f=1MHz		1.1	1.6	MHz

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified





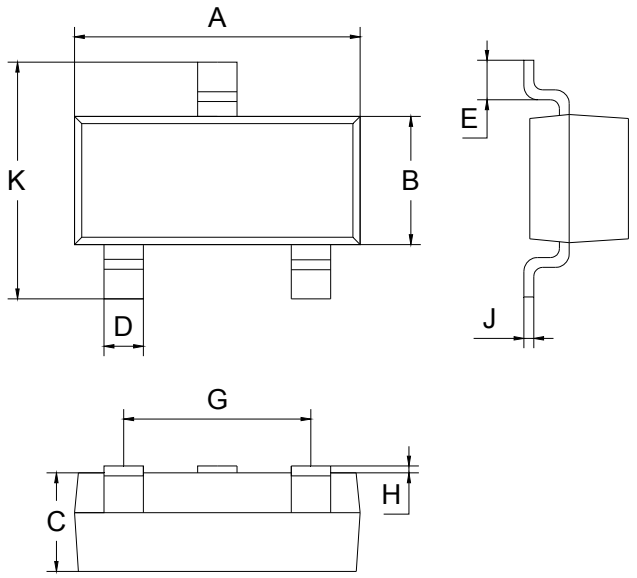




Silicon Epitaxial Planar Transistor **2SC3125**

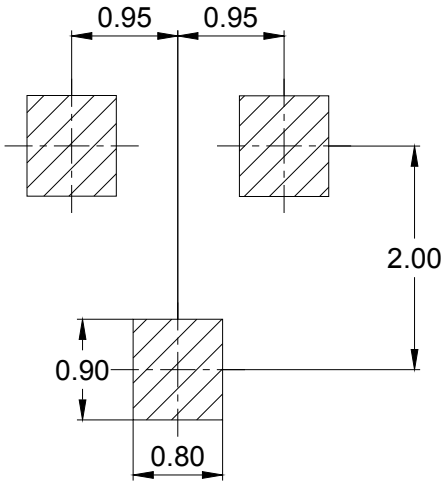
PACKAGE OUTLINE

Plastic surface mounted package SOT-23



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SC3125	SOT-23	3000/Tape&Reel